

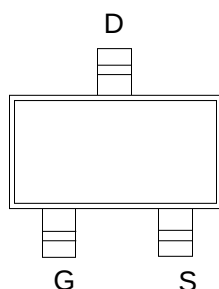
100V/2.3A N-Channel MOSFET

Features

- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Application

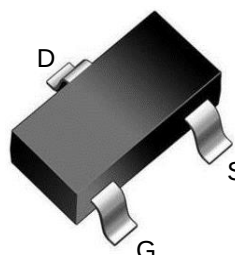
- DC-DC Converters
- Power management functions



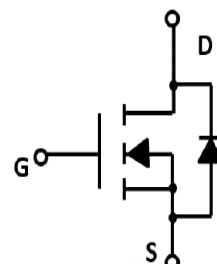
Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
100V	234mΩ@10V	2.3A
	278mΩ@4.5V	



SOT-23 top view



Schematic diagram



Pb-Free



RoHS



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

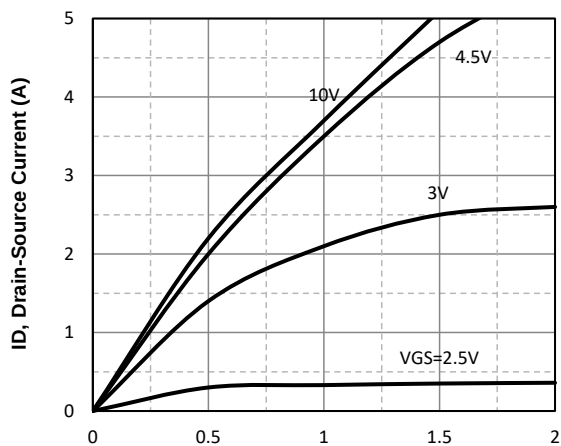
V_{DS}	Drain-Source Breakdown Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 2.3	A

Mounted on Large Heat Sink

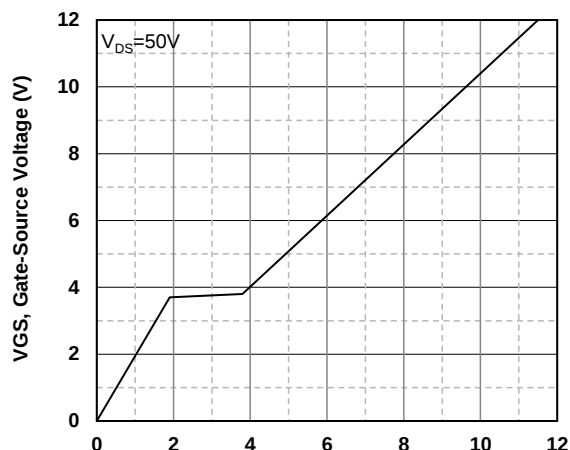
I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ 9	A
I_D	Continuous Drain Current@GS=10V	$T_C=25^\circ\text{C}$ 2.3	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 1.3	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient(*1 in2 Pad of 2-oz Copper), Max.)	96	°C/W

Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	VGS=0V, ID=250μA	100	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=100V, VGS=0V	--	--	1	uA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.0	1.8	2.5	V
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=2A	--	195	234	mΩ
		VGS=4.5V, ID=1A	--	230	278	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
CISS	Input Capacitance	VDS=10V, VGS=0V, f=1MHz	--	387	--	pF
COSS	Output Capacitance		--	30	--	pF
CRSS	Reverse Transfer Capacitance		--	28	--	pF
Switching Characteristics						
Qg	Total Gate Charge	VDS=50V, ID=2A, VGS=10V	--	9.5	--	nC
Qgs	Gate Source Charge		--	1.8	--	nC
Qgd	Gate Drain Charge		--	2	--	nC
td(on)	Turn-on Delay Time	VDS=50V, ID=1.3A, VGS=10V, RG=1Ω	--	4	--	nS
tr	Turn-on Rise Time		--	17.5	--	nS
td(off)	Turn-Off Delay Time		--	13	--	nS
tf	Turn-Off Fall Time		--	28	--	nS
Source- Drain Diode Characteristics						
VSD	Forward on voltage	Tj=25°C, Is=2A,	--	--	1.2	V

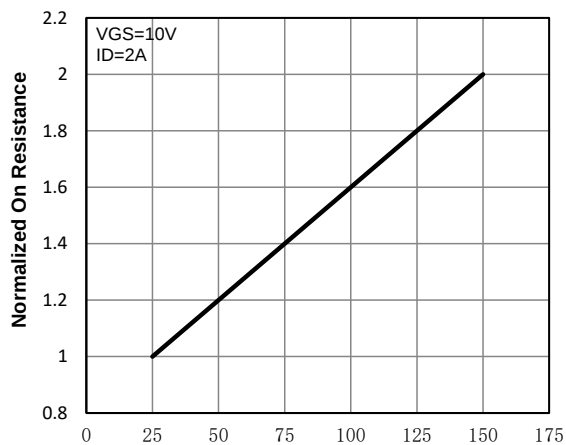
Typical Operating Characteristics



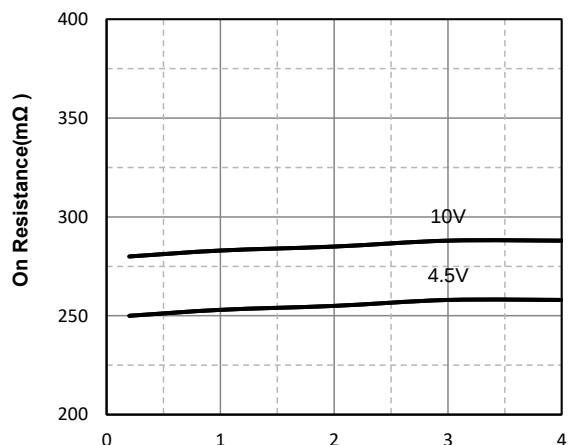
VDS, Drain -Source Voltage (V)
Fig1. Typical Output Characteristics



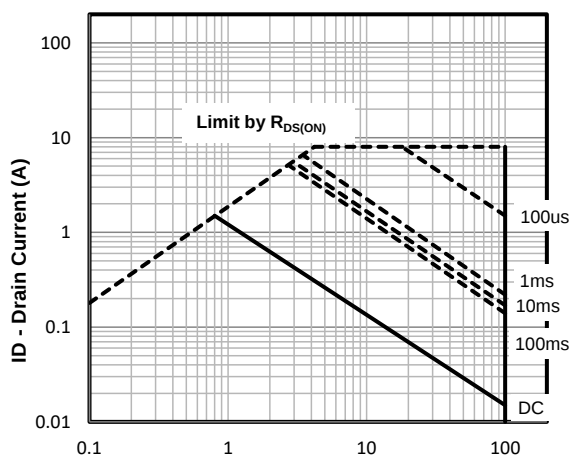
Qg -Total Gate Charge (nC)
Fig2. Typical Gate Charge Vs. Gate-Source Voltage



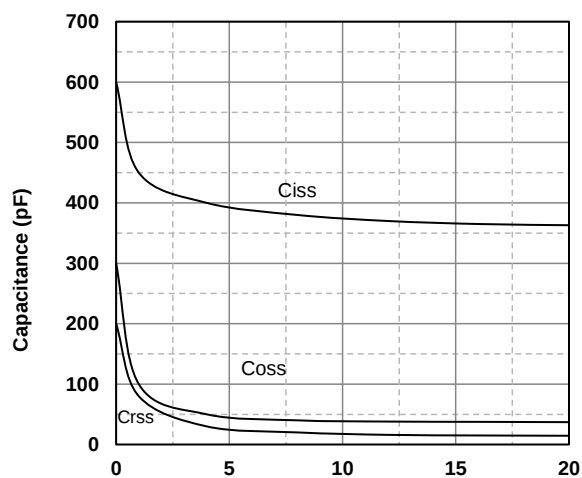
Tj - Junction Temperature (°C)
Fig3. Normalized On-Resistance Vs. Temperature



ID, Drain-Source Current (A)
Fig4. On-Resistance Vs. Drain-Source Current

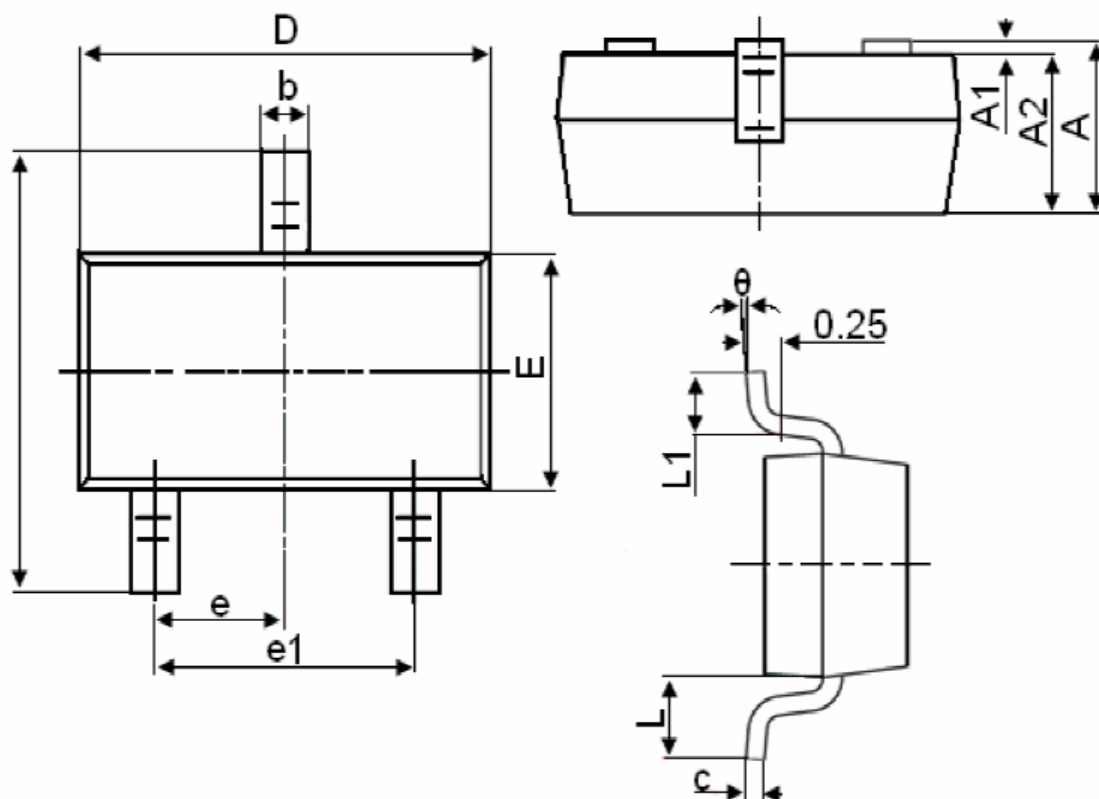


VDS, Drain -Source Voltage (V)
Fig5. Maximum Safe Operating Area



VDS, Drain-Source Voltage (V)
Fig6. Typical Capacitance Vs. Drain-Source Voltage

SOT-23 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°